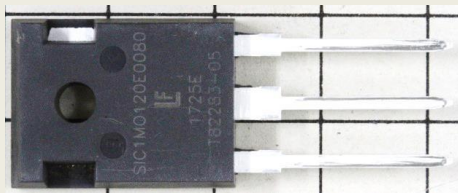


ANALYSIS REPORT THE LITTELFUSE 'LSIC1MO120E0080' 1st GENERATION 1200V SiC POWER MOSFET

February 2018. LTEC Corporation released a detailed structure and process analysis report of this 1200V silicon carbide MOSFET, the 1st product from Littelfuse.

Littelfuse invested in SiC technology development company 'Monolith Semiconductor' in March 2017 in order to strengthen power semiconductor field. This product is reported as the first SiC MOSFET designed, developed and manufactured by its partnership.



Package top view



Die top view

Device features

- Max. operating voltage: 1200V, rated DC Drain current $I_D=39A$ at $T_j=25^\circ C$
- ON-resistance, $R_{ON} \times A= 562m\Omega \times mm^2$ (Temperature dependence is lower than competitors')

The report has two individually purchasable sections: an 95-page Structure Analysis, and a 24-page Process Analysis section. The Structure Analysis section reveals the physical construction of the device, including EDX materials analysis, and many other fine details. The Process Analysis section includes manufacturing process flow, the estimated number of photomasking steps, and the comparison with Rohm, Wolfspeed and Infineon products.

Structure analysis report: \$4,600

Process analysis report: \$4,600

Note: The listed report price may not be accurate as it decreases over time.

Please contact us for current report pricing : info@ltecusa.com

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